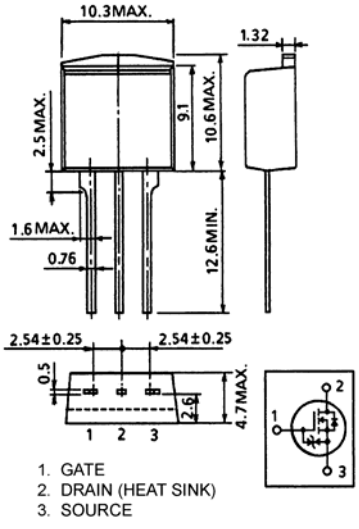
TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (L^2−π−MOSV)

2SK2311

Chopper Regulator, DC−DC Converter and Switching Regulator Applications

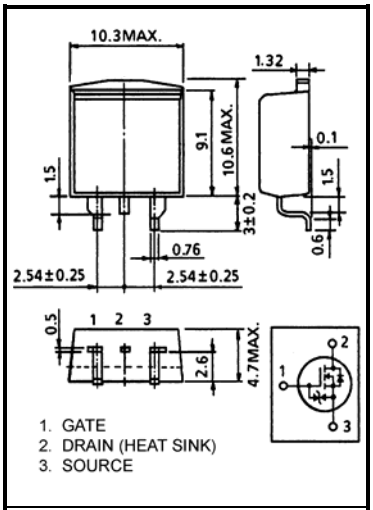
- 4-V gate drive
- Low drain−source ON resistance : $R_{DS\ (ON)}$ = 36 mΩ (typ.)
- High forward transfer admittance : $|Y_{fs}|$ = 16 S (typ.)
- Low leakage current : I_{DSS} = 100 μA (max) (V_{DS} = 60 V)
- Enhancement mode : V_{th} = 0.8~2.0 V (V_{DS} = 10 V, I_D = 1 mA)

Unit: mm



JEDEC	—
JEITA	—
TOSHIBA	2-10S1B

Weight: 1.5 g (typ.)



JEDEC	—
JEITA	—
TOSHIBA	2-10S2B

Weight: 1.5 g (typ.)

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain−source voltage		V_{DSS}	60	V
Drain−gate voltage (R_{GS} = 20 kΩ)		V_{DGR}	60	V
Gate−source voltage		V_{GSS}	±20	V
Drain current	DC (Note 1)	I_D	25	A
	Pulse (Note 1)	I_{DP}	100	A
Drain power dissipation (Tc = 25°C)		P_D	40	W
Single pulse avalanche energy (Note 2)		E_{AS}	156	mJ
Avalanche current		I_{AR}	25	A
Repetitive avalanche energy (Note 3)		E_{AR}	3.5	mJ
Channel temperature		T_{ch}	150	°C
Storage temperature range		T_{stg}	−55~150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook (“Handling Precautions”/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th\ (ch-c)}$	3.125	°C / W
Thermal resistance, channel to ambient	$R_{th\ (ch-a)}$	83.3	°C / W

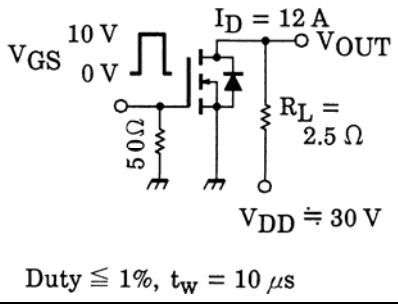
Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V_{DD} = 25 V, T_{ch} = 25°C (initial), L = 339 μH, R_G = 25 Ω, I_{AR} = 25 A

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device.
Please handle with caution.

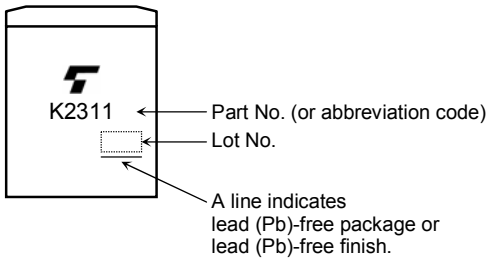
Electrical Characteristics (Ta = 25°C)

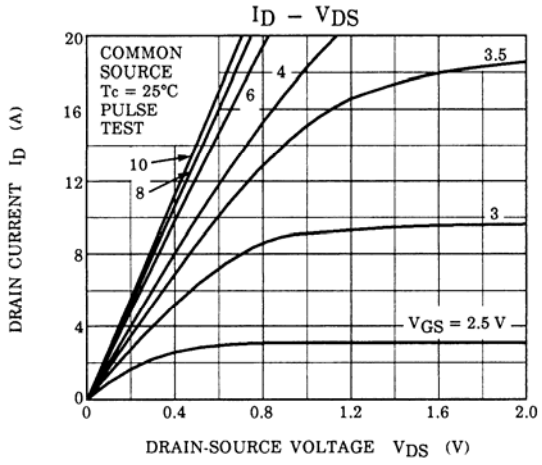
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	V_{GS} = ±16 V, V_{DS} = 0 V	—	—	±10	μA
Drain cut−off current		I_{DSS}	V_{DS} = 60 V, V_{GS} = 0 V	—	—	100	μA
Drain−source breakdown voltage		$V_{(BR)\ DSS}$	I_D = 10 mA, V_{GS} = 0 V	60	—	—	V
Gate threshold voltage		V_{th}	V_{DS} = 10 V, I_D = 1 mA	0.8	—	2.0	V
Drain−source ON resistance		$R_{DS\ (ON)}$	V_{GS} = 4 V, I_D = 12 A	—	57	80	mΩ
			V_{GS} = 10 V, I_D = 12 A	—	36	46	
Forward transfer admittance		$\|Y_{fs}\|$	V_{DS} = 10 V, I_D = 12 A	10	16	—	S
Input capacitance		C_{iss}	V_{DS} = 10 V, V_{GS} = 0 V, f = 1 MHz	—	1000	—	pF
Reverse transfer capacitance		C_{rss}		—	200	—	
Output capacitance		C_{oss}		—	550	—	
Switching time	Rise time	t_r		—	20	—	ns
	Turn−on time	t_{on}		—	30	—	
	Fall time	t_f		—	55	—	
	Turn−off time	t_{off}		—	130	—	
Total gate charge (Gate−source plus gate−drain)		Q_g	V_{DD} ≈ 48 V, V_{GS} = 10 V, I_D = 25 A	—	38	—	nC
Gate−source charge		Q_{gs}		—	25	—	
Gate−drain (“miller”) charge		Q_{gd}		—	13	—	

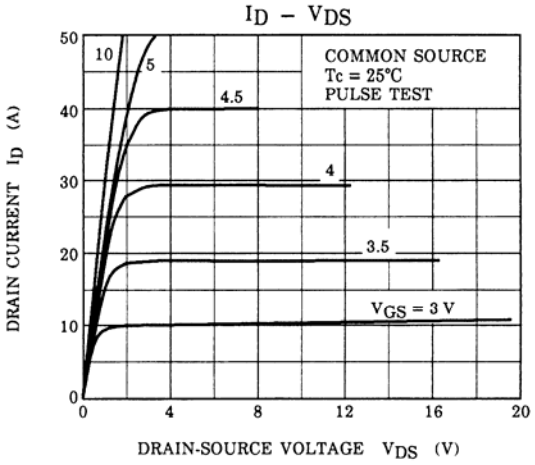
Source−Drain Ratings and Characteristics (Ta = 25°C)

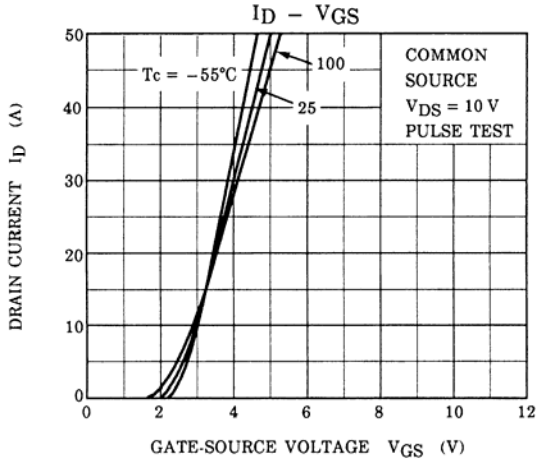
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	I_{DR}	—	—	—	25	A
Pulse drain reverse current (Note 1)	I_{DRP}	—	—	—	100	A
Forward voltage (diode)	V_{DSF}	I_{DR} = 25 A, V_{GS} = 0 V	—	—	−1.8	V
Reverse recovery time	t_{rr}	I_{DR} = 25 A, V_{GS} = 0 V dI_{DR} / dt = 50 A / μs	—	50	—	ns
Reverse recovery charge	Q_{rr}		—	35	—	μC

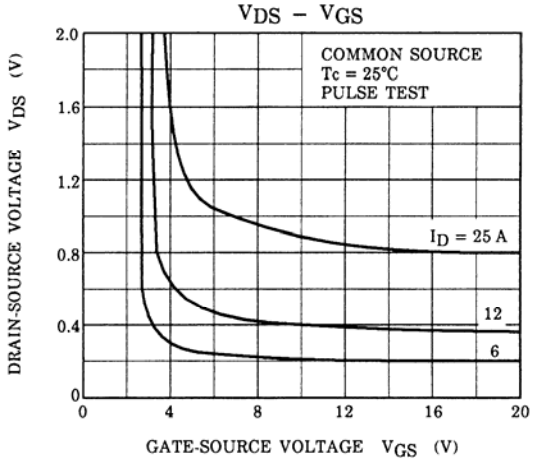
Marking

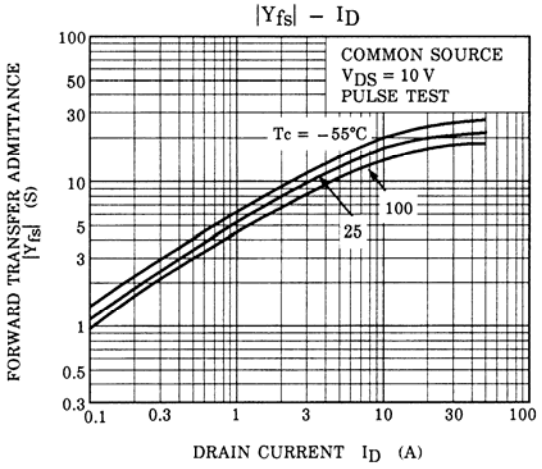


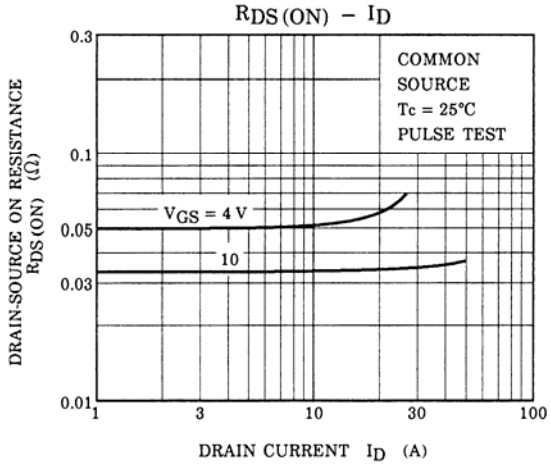

I_D – V_{DS}
COMMON SOURCE
Tc = 25°C
PULSE TEST
3.5
4
6
10
8
3
V_{GS} = 2.5 V
DRAIN CURRENT I_D (A)
DRAIN-SOURCE VOLTAGE V_{DS} (V)

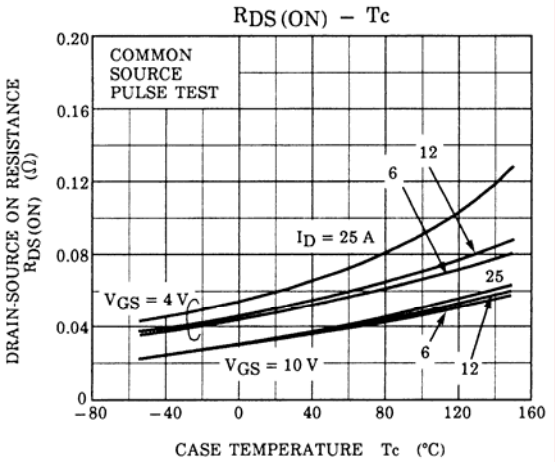

I_D – V_{DS}
10
5
4.5
4
3.5
COMMON SOURCE
Tc = 25°C
PULSE TEST
V_{GS} = 3 V
DRAIN CURRENT I_D (A)
DRAIN-SOURCE VOLTAGE V_{DS} (V)

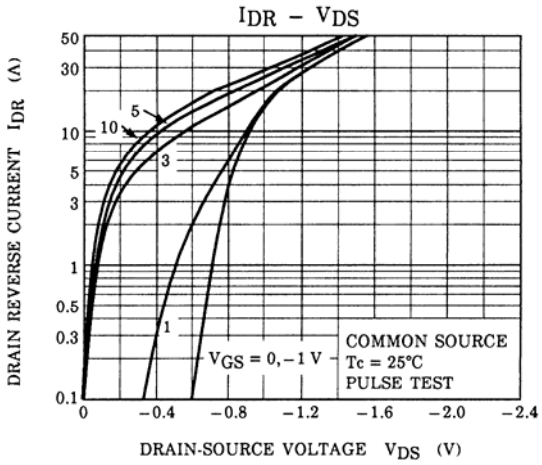

I_D – V_{GS}
Tc = −55°C
100
25
COMMON SOURCE
V_{DS} = 10 V
PULSE TEST
DRAIN CURRENT I_D (A)
GATE-SOURCE VOLTAGE V_{GS} (V)

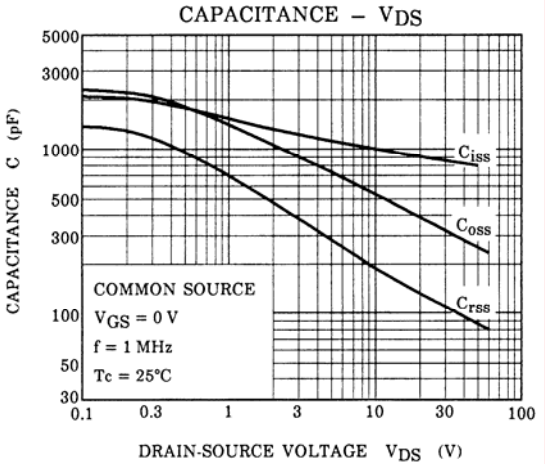

V_{DS} – V_{GS}
COMMON SOURCE
Tc = 25°C
PULSE TEST
I_D = 25 A
12
6
DRAIN-SOURCE VOLTAGE V_{DS} (V)
GATE-SOURCE VOLTAGE V_{GS} (V)

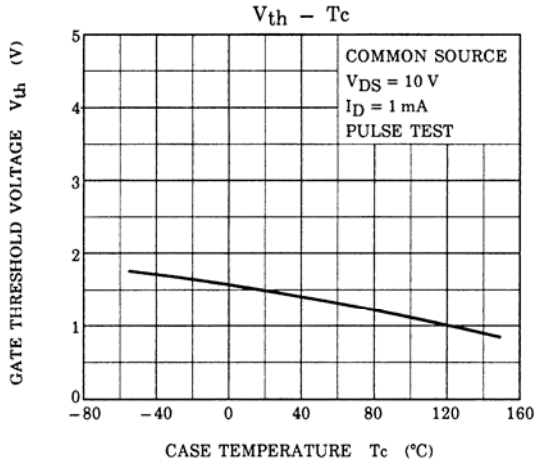

$|Y_{fs}|$ – I_D
COMMON SOURCE
V_{DS} = 10 V
PULSE TEST
Tc = −55°C
100
25
FORWARD TRANSFER ADMITTANCE $|Y_{fs}|$ (S)
DRAIN CURRENT I_D (A)

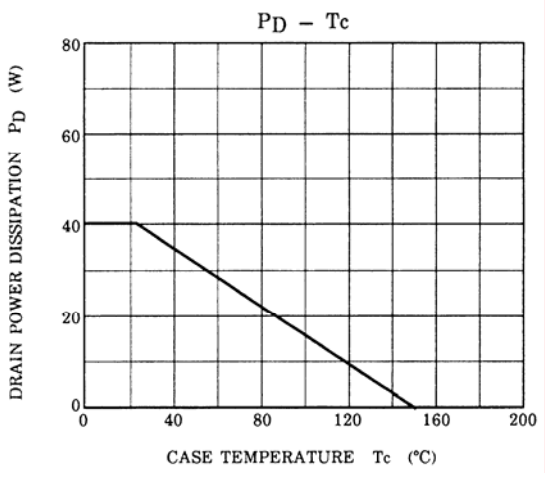

$R_{DS\,(ON)}$ – I_D
COMMON SOURCE
Tc = 25°C
PULSE TEST
V_{GS} = 4 V
10
DRAIN-SOURCE ON RESISTANCE $R_{DS\,(ON)}$ (Ω)
DRAIN CURRENT I_D (A)

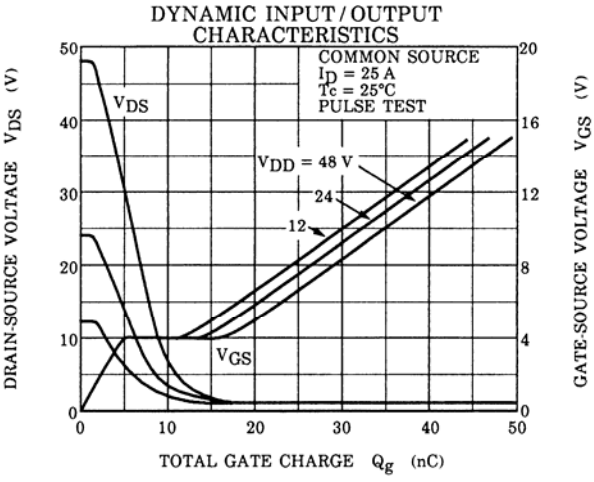

$R_{DS(ON)}$ – Tc
COMMON SOURCE PULSE TEST
I_D = 25 A
V_{GS} = 4 V
V_{GS} = 10 V
12
6
25
DRAIN-SOURCE ON RESISTANCE $R_{DS(ON)}$ (Ω)
CASE TEMPERATURE Tc (°C)

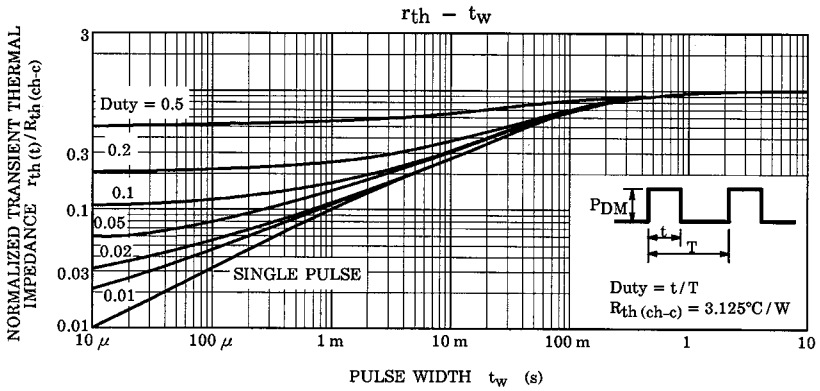

I_{DR} – V_{DS}
COMMON SOURCE
Tc = 25°C
PULSE TEST
V_{GS} = 0, −1 V
DRAIN REVERSE CURRENT I_{DR} (A)
DRAIN-SOURCE VOLTAGE V_{DS} (V)

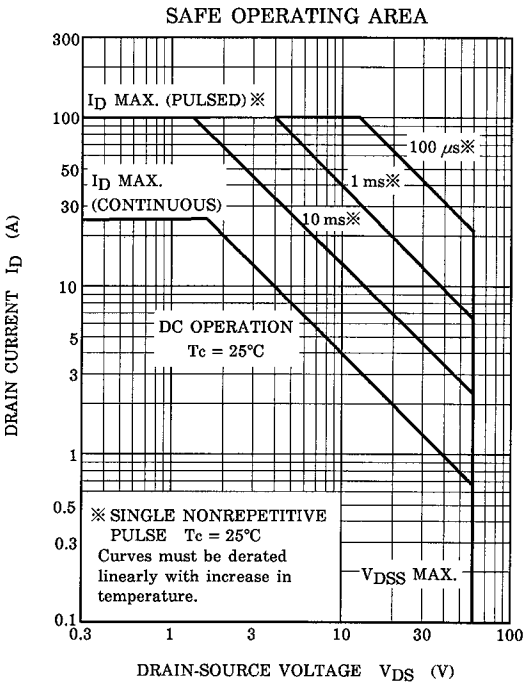

CAPACITANCE – V_{DS}
C_{iss}
C_{oss}
C_{rss}
COMMON SOURCE
V_{GS} = 0 V
f = 1 MHz
Tc = 25°C
CAPACITANCE C (pF)
DRAIN-SOURCE VOLTAGE V_{DS} (V)

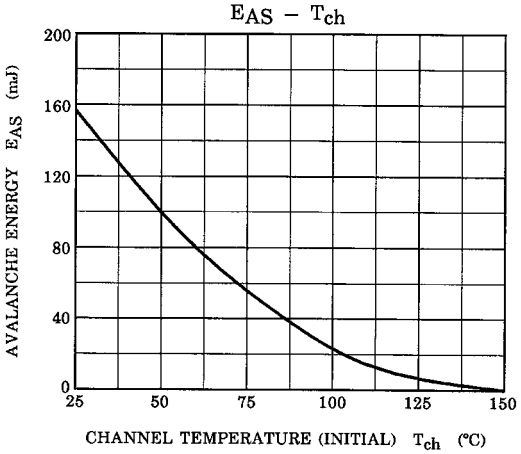

V_{th} – Tc
COMMON SOURCE
V_{DS} = 10 V
I_D = 1 mA
PULSE TEST
GATE THRESHOLD VOLTAGE V_{th} (V)
CASE TEMPERATURE Tc (°C)

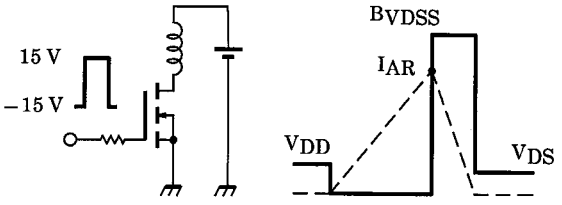

P_D – Tc
DRAIN POWER DISSIPATION P_D (W)
CASE TEMPERATURE Tc (°C)


DYNAMIC INPUT / OUTPUT CHARACTERISTICS
COMMON SOURCE
I_D = 25 A
Tc = 25°C
PULSE TEST
V_{DS}
V_{GS}
V_{DD} = 48 V
24
12
DRAIN-SOURCE VOLTAGE V_{DS} (V)
GATE-SOURCE VOLTAGE V_{GS} (V)
TOTAL GATE CHARGE Q_g (nC)









TEST CIRCUIT WAVE FORM

$R_G = 25\ \Omega$
$V_{DD} = 25$ V, L = 339 μH

$$EAS = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

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